



2814

Attorney Docket No.: 5649-926

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Kim et al.

Serial No.: 10/054,540

Filed: January 22, 2002

For: INTEGRATED CIRCUIT FERROELECTRIC MEMORY DEVICES INCLUDING
PLATE LINES DIRECTLY ON FERROELECTRIC CAPACITORS AND
METHODS OF FABRICATING THE SAME

Confirmation No.: 5971

Examiner: H. Pham

Group Art Unit: 2814

8/02
H. Pham
2-13-03

Date: February 5, 2003

BOX NON-FEE AMENDMENT

Commissioner for Patents

Washington, DC 20231

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AMENDMENT

Sir:

This Amendment is responsive to the Official Action of November 6, 2002. The claims have been amended herein using the replacement claims format. The present amendment also includes a section entitled "**VERSION WITH MARKINGS TO SHOW CHANGES MADE**" attached hereto.

In the title:

Please replace the title with the following new title:

--INTEGRATED CIRCUIT FERROELECTRIC MEMORY DEVICES INCLUDING
PLATE LINES DIRECTLY ON FERROELECTRIC CAPACITORS--

In the Claims:

Please replace the now pending Claim 1 with the following like number claim.

1. (Amended) An integrated circuit ferroelectric memory device, comprising:
an integrated circuit transistor;
a ferroelectric capacitor on the integrated circuit transistor having first and second
sidewalls, the ferroelectric capacitor including a first electrode adjacent the transistor, a
second electrode remote from the transistor and a ferroelectric film therebetween;

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an insulating layer on the first and second sidewalls of the ferroelectric capacitor, the insulating layer having a surface that is substantially coplanar with an upper surface of the second electrode; and

a plate line directly on the ferroelectric capacitor.
